

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI SD1460** is Designed for Class C, FM Broadcast Applications up to 108 MHz.

**FEATURES:**

- Class C Operation
- $P_G = 9.0$  dB at 150 W/108 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	16 A
$V_{CBO}$	60 V
$V_{CEO}$	25 V
$V_{CES}$	60 V
$V_{EBO}$	4.0 V
$P_{DISS}$	230 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	1.1 $^\circ C/W$

**PACKAGE STYLE .500 4L FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K	.280 / 7.11	
L	.980 / 24.89	1.050 / 26.67

**ORDER CODE: ASI10588**

**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 100$ mA	60			V
$BV_{CER}$	$I_C = 100$ mA $R_{BE} = 10 \Omega$	55			V
$BV_{CEO}$	$I_C = 100$ mA	25			V
$BV_{EBO}$	$I_E = 20$ mA	4.0			V
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	20		150	---
$C_{OB}$	$V_{CB} = 28$ V $f = 1.0$ MHz			140	pF
$P_G$ $\eta_c$	$V_{CC} = 28$ V $P_{OUT} = 150$ W $f = 108$ MHz	9.0	65		dB %